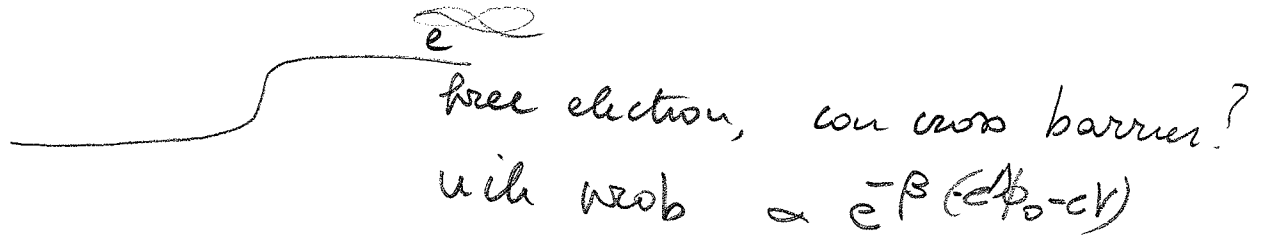


# ELECTRON GENERATION



promoted by thermal population, if get close to junction is swept in ~~add~~ by potential ( $\Delta\phi$ ) (independent by  $V$ )  
 $J_e^{gen}$   
 all  $e^-$  that cross get caught

# ELECTRON RECOMBINATION



free electron, can cross barrier?

with prob  $\propto e^{-\beta(\epsilon\phi_0 - eV)}$

$$\Rightarrow J_e^{rec} \propto e^{-\beta(\epsilon\phi_0 - eV)}$$

$$\Rightarrow J_e^{rec}(V=0) = J_e^{gen} \quad \text{steady state}$$

$\Rightarrow$  to write

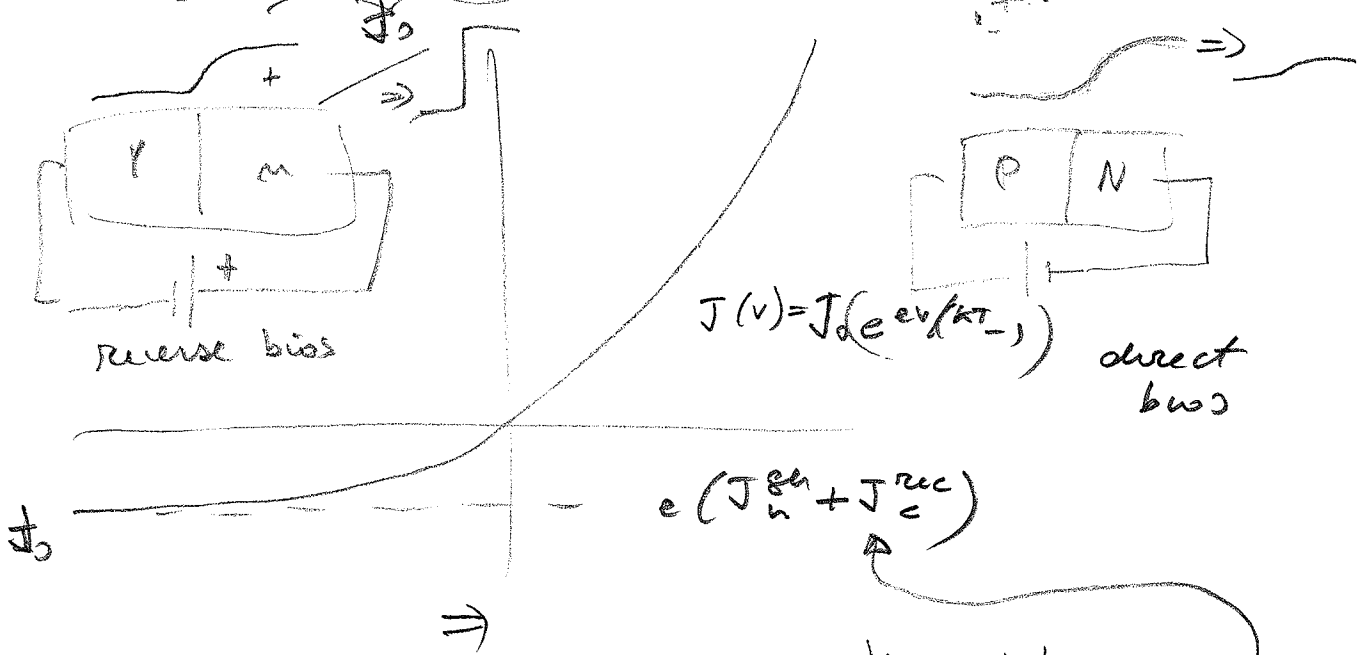
$$J_e = (J_e^{rec} - J_e^{gen}) = J_e^{gen} (e^{eV/kT} - 1)$$

(remember electrons have charge  $(-e)$ , but they live in  $\phi$  in the place where voltage is  $-V$ !!)

⇒ tot  $J$  is

$$J = -eJ_e + eJ_h = e(J_h - J_e)$$

$$= e \underbrace{(J_h^{ge} + J_e^{ge})}_{J_0} \left( e^{eV/kT} - 1 \right)$$



$$J(V) = J_0 \left( e^{eV/kT} - 1 \right)$$

direct bias

$$e(J_h^{ge} + J_e^{rec})$$

remember  $e\Delta\phi_0$  inside

$$e\Delta\phi = E_{gap} + kT \log \left( \frac{N_d N_a}{N_c(T) P_v(T)} \right)$$

the recombination current. The number of such holes is proportional to  $e^{-e\Delta\phi/k_B T}$  and therefore<sup>11</sup>

$$J_h^{\text{rec}} \propto e^{-e[(\Delta\phi)_0 - V]/k_B T}. \quad (29.22)$$

In contrast to the generation current, the recombination current is highly sensitive to the applied voltage  $V$ . We can compare their magnitudes by noting that when  $V = 0$  there can be no net hole current across the junction:

$$J_h^{\text{rec}}|_{V=0} = J_h^{\text{gen}}. \quad (29.23)$$

Taken together with Eq. (29.22), this requires that

$$J_h^{\text{rec}} = J_h^{\text{gen}} e^{eV/k_B T}. \quad (29.24)$$

The total current of holes flowing from the  $p$ - to the  $n$ -side of the junction is given by the recombination current minus the generation current:

$$J_h = J_h^{\text{rec}} - J_h^{\text{gen}} = J_h^{\text{gen}}(e^{eV/k_B T} - 1). \quad (29.25)$$

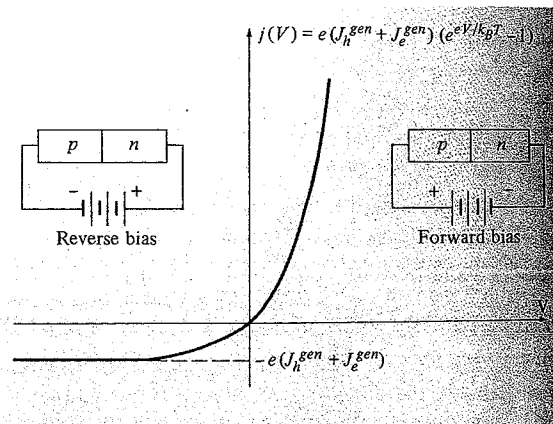
The same analysis applies to the components of the electron current, except that the generation and recombination currents of electrons flow oppositely to the corresponding currents of holes. Since, however, the electrons are oppositely charged, the electrical generation and recombination currents of electrons are parallel to the electrical generation and recombination currents of holes. The total electrical current density is thus:

$$j = e(J_h^{\text{gen}} + J_e^{\text{gen}})(e^{eV/k_B T} - 1). \quad (29.26)$$

This has the highly asymmetric form characteristic of rectifiers, as shown in Figure 29.5.

Figure 29.5

Current vs. applied voltage  $V$  for a  $p$ - $n$  junction. The relation is valid for  $eV$  small compared with the energy gap,  $E_g$ . The saturation current  $(eJ_h^{\text{gen}} + eJ_e^{\text{gen}})$  varies with temperature as  $e^{-E_g/k_B T}$ , as established below.



<sup>11</sup> In assuming that (29.22) gives the dominant dependence of the hole recombination current on  $V$ , we are assuming that the density of holes just on the  $p$ -side of the depletion layer differs only slightly from  $N_a$ . We shall find that this is also the case provided that  $eV$  is small compared with the energy gap  $E_g$ .

## GENERAL PHY

The foregoing discussion appearing in (29.2) densities will not in equilibrium Maxwell analysis to constrain transition region the case.

In this more detailed and hole currents. Instead, at each point equations relating and hole densities field,  $E(x) = -dq$  principle, to find approach we follow the electron and hole equations we use  $n_e(x)$  and  $p_e(x)$  to be viewed as the relation (29.3), with

We first observe gradient, the carrier to the field (the diffusion current)

The positive<sup>12</sup> known as the electric than writing the in which the drift density are present  $ne^2\tau/m$  for the conductivity

<sup>12</sup> The signs in along the field, and

NON EQUILIBRIUM CASE  $\Rightarrow$  goes to equilibrium

we saw Electric field  $\phi \leftrightarrow V \rightarrow$  current  
 in thermodynamical equilibrium

but what about current due by  $\nabla$  gradient of concentrations?

$\sigma = \underbrace{\mu}_{\text{mobility}} \underbrace{ne}_{\text{density}} \Rightarrow \mathbf{J} = \underbrace{\mu}_{\text{charge}} ne \mathbf{E}$   $\leftarrow$  field

but EM field is  $E = -\nabla\phi$   $\leftarrow$  potential

and for I can about current of particles.

$\Rightarrow \mathbf{J}_e = \frac{\mathbf{J}_e}{-e} \Rightarrow \mathbf{J}_e = \mu_e n \nabla\phi$   
 $\mathbf{J}_p = -\mu_p p \nabla\phi$  of equilibrium  $n, p$  const  
holes, electrons mobilities

but for  $n, p$  was constant in  $x$ ?  $\Rightarrow$  diffusion

$\Rightarrow$  drift current proportional to  $\nabla$  concentration

(Thus,  $\nabla_{\text{pot}}$  (Klein pot) but small concentration  $\Rightarrow n \approx \mu$ )

$\Rightarrow$  drift  $e \sim -D_n \nabla n(x)$

drift  $h \sim -D_p \nabla p(x)$

$D_n, D_p$

electrons & holes diffusion constant.

carrier collision times

remember  $J = \sigma E = -e J_e = -e \mu_n n E \Rightarrow$

$J_e = \mu_e n \nabla\phi - D_n \nabla n(x)$   
 $J_p = -\mu_p p \nabla\phi - D_p \nabla p(x)$

$\sigma = \frac{ne^2 \tau}{m} = \mu ne \Rightarrow \mu_e = \frac{e \tau_n}{m_n^*}$

$\mu_p = \frac{e \tau_p}{m_p^*}$

numbers, will hold (the self consistent one)

$$n_c(x) = N_c(t) e^{-\beta(E_c - \mu - e\phi(x))}$$

$$P_o(x) = P_v(t) e^{-\beta(\mu - E_v + e\phi(x))}$$

$$\Rightarrow \nabla n = n(\beta e \nabla \phi)$$

$$\nabla p = p(-\beta e \nabla \phi)$$

$\Rightarrow$  in equilibrium

$$0 = J_e = \mu_e n \nabla \phi - D_n n \beta e \nabla \phi = 0$$

$$0 = J_p \Rightarrow$$

$$\Rightarrow \begin{cases} \mu_e = \frac{D_n e}{kT} \\ \mu_p = + \frac{D_p e}{kT} \end{cases}$$

EINSTEIN RELATIONS

always find something similar

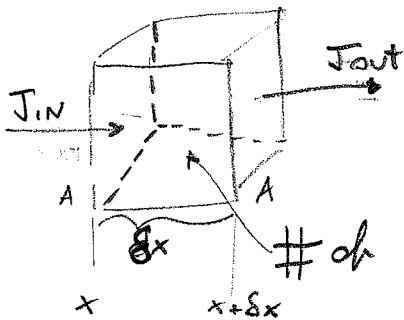
when you have 2 phenomena:

- transport due by field ( $\Rightarrow v_{drift}$ )
- drift, diffusion  $\Rightarrow \dots$

EXPRESS  $\frac{\partial n(x)}{\partial t}$  in function of  $\nabla_x J$

for  $V=0 \Rightarrow J_e = J_h = 0 \Rightarrow$  thermodynamic equilibrium, steady state,

but when  $V \neq 0$   $\left[ \int_{-\infty}^{+\infty} \phi \rightarrow \phi(+\infty) - \phi(-\infty) \right]$



lets

if  $J_{in} = J_{out} \Rightarrow$  # particles inside = constant

$$N = n \text{ Volume} \Rightarrow n A \delta x$$

but if  $J_{in} \neq J_{out}$  ?

$$\delta x \text{ small} \Rightarrow \text{Taylor} \quad J_{out}(x) = J_{in}(x) + \frac{\partial J}{\partial x} \delta x \Rightarrow$$

Flux in per unit time  $\Rightarrow$

$$J_{in}(x) A$$

Flux out per unit time

$$J_{out}(x) A = J_{in}(x) A + A \frac{\partial J}{\partial x} \delta x$$

$\Rightarrow$   $n$  particles

$$\left( \begin{array}{l} \text{Flux in} - \text{Flux out} \\ \text{(per unit time)} \end{array} \right) = \frac{\partial N}{\partial t} = \underbrace{(A \delta x)}_{\text{volume}} \frac{\partial n(x)}{\partial t}$$

CONSERVATION OF CARRIERS, THEY DO NOT DIE, JUST EXIT

$$\Rightarrow \cancel{J_{in} A} - \cancel{J_{in} A} + A \frac{\partial J}{\partial x} \delta x = A \delta x \frac{\partial n(x)}{\partial t}$$

$$\boxed{\begin{array}{l} \frac{\partial n_c(x)}{\partial t} = - \frac{\partial J_e(x)}{\partial x} \\ \& \frac{\partial p_v(x)}{\partial t} = - \frac{\partial J_h(x)}{\partial x} \end{array}}$$

← particles number ch. →

CONTINUITY EQUATIONS

$\& V \neq 0 +$  fluctuations given by T

But carriers are not conserved due by thermal activation

$$\frac{\partial n_c(x)}{\partial t} = - \frac{\partial J_e}{\partial x} + \left[ \frac{dn_c(x)}{dt} \right]_{g \rightarrow r}$$

$$\frac{\partial p_v(x)}{\partial t} = - \frac{\partial J_h}{\partial x} + \left[ \frac{dp_v(x)}{dt} \right]_{g \rightarrow r}$$

✓

restore equilibrium when carrier densities go out

$\& n_c > n_c^* (eq) \Rightarrow rec > gen \Rightarrow n \rightarrow n^*$   
and vice versa, and for p.

of equilibrium

In regions where  $n_c$  &  $p_v$  exceed their equilibrium values, recombination occurs faster than generation, leading to a decrease in carrier densities, while in regions where they fall short of their equilibrium values, generation occurs faster than recombination, leading to an increase in the carrier density. NICE

⇒ how to model? with DRIVE recomb time

$$\Rightarrow \left( \frac{dn_c(x)}{dt} \right)_{\text{gen rec}} = - \frac{(n_c - n_c^0)}{\tau_n} \quad \left( - \text{because } \text{if } n > n^0 \Rightarrow \frac{dn}{dt} < 0 \right)$$

$$\left( \frac{dp_v(x)}{dt} \right)_{\text{gen rec}} = - \frac{(p_v - p_v^0)}{\tau_p}$$

lifetimes  $\gg$  relaxation times

$n_c^0, p_v^0(x)$  are the ones given by the  $\phi(x)$ !!

$$\Rightarrow dn_c = -n_c \frac{dt}{\tau_n} - \frac{n_c^0}{\tau_n} dt$$

through total generation

$$\Rightarrow n_c(t+dt) = n_c(t) \left( 1 - \frac{dt}{\tau_n} \right) - \frac{n_c^0}{\tau_n} dt$$

$\tau_n, \tau_p \gg \tau_n^{\text{coll}}, \tau_p^{\text{coll}}$

lifetime of recombination/generation

of interband transition

given by  $\tau \propto T^{\frac{1}{2}}$  Temperature

$\tau_n, \tau_p \sim 10^{-3}, 10^{-8}$  sec

$\tau_n^{\text{coll}}, \tau_p^{\text{coll}} \sim 10^{-12}, 10^{-13}$  sec

> destruction of a fraction  $\frac{dt}{\tau_n}$  of the present electrons

> creation of a fraction  $\frac{dt}{\tau_n}$  of the equilibrium electrons

⇒ eqs are out of eq,  $V \neq 0$   
with fluctuations due by T

$$\frac{\partial m_c(x,t)}{\partial t} + \frac{\partial J_e(x,t)}{\partial x} + \frac{m_c(x,t) - m_c^0}{\tau_m} = 0$$

$$\frac{\partial P_v(x,t)}{\partial t} + \frac{\partial J_h(x,t)}{\partial x} + \frac{P_v(x,t) - P_v^0}{\tau_p} = 0$$

→ STEADY STATE (still  $V, \& T$ , but "sustained state")

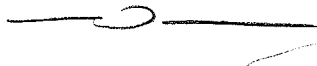
$$\frac{\partial J_e}{\partial x} + \frac{m_c(x) - m_c^0(x)}{\tau_m} = 0$$

← equilibrium profile } known  $\phi$  slope

$$\frac{\partial J_h}{\partial x} + \frac{P_v(x) - P_v^0(x)}{\tau_p} = 0$$

← equilibrium profile with fluctuations due by T

eq replaced  $J_e = J_h = 0$   
when  $V \neq 0$



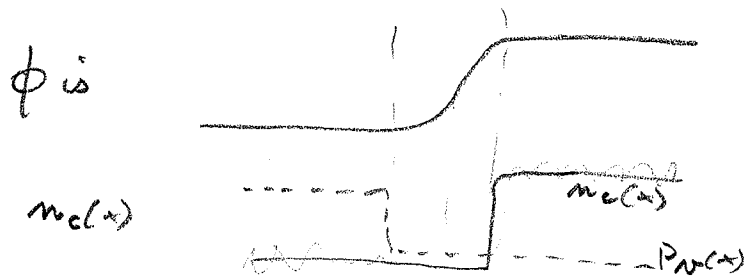
draft

remember

$$J_e = \mu_c m_c \nabla \phi - D_m \nabla m_c(x)$$

$$J_h = -\mu_p P_v \nabla \phi - D_p \nabla P_v(x)$$

diffusion



outside depletion region  $\phi$  is const

$$\Rightarrow J_e \approx -D_m \nabla m_c(x)$$

$$J_h \approx -D_p \nabla P_v(x)$$



$$\Rightarrow \frac{\partial J_e}{\partial x} \approx -D_n \frac{\partial^2 n_c(x)}{\partial x^2} \quad \text{same for } P_n$$

$$\Rightarrow \underbrace{D_n \frac{\partial^2 n_c(x)}{\partial x^2}}_{z_n} = \underbrace{\frac{n_c(x) - n_c^0(x)}{z_n}}_{z_n}$$

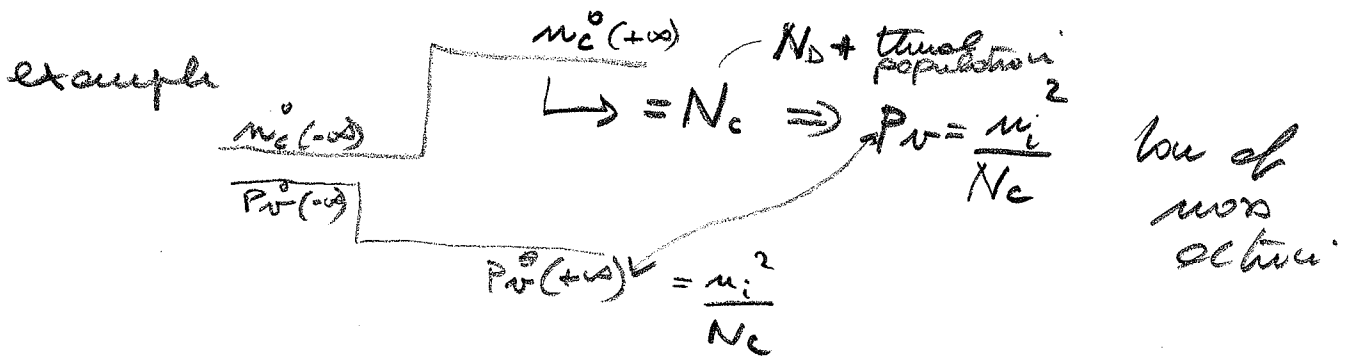
$$D_p \frac{\partial^2 P_n(x)}{\partial x^2} = \frac{P_n(x) - P_n^0(x)}{z_p}$$

Solutions vary exponentially in  $\frac{x}{L}$

with  $L_n = \sqrt{D_n z_n}$   
 $L_p = \sqrt{D_p z_p}$

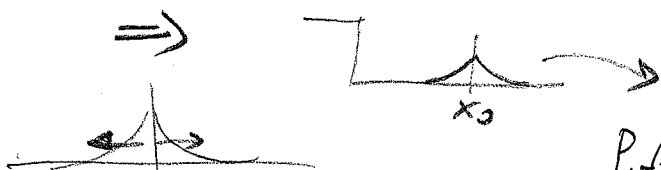
diffusion length

$\Rightarrow$  space it takes to reequilibrate to  $n_c^0, P_n^0$  values



if I vary because some hole generated by T @  $x_0$

$$P_n(x_0) \neq P_n^0(+\infty)$$



$$P_n(x) = P_n^0(+\infty) + [P_n(x_0) - P_n^0(+\infty)] e^{-\frac{|x-x_0|}{L_p}}$$

S41

holes generated by T or Light or injection, wander around until recombine  $\Rightarrow$  How?

Remember Einstein relations

$$\begin{aligned} \mu_e &= \frac{D_m e}{kT} \\ \mu_p &= \frac{D_p e}{kT} \end{aligned} \Rightarrow \Rightarrow D_m = \frac{kT \mu_e}{e} \quad (\text{same for } D_p)$$

remember  $\sigma = \mu_0 m_c e = \frac{n_c e^2 z_m^{coll}}{m^*} \Rightarrow \mu_e = \frac{e z_m^{coll}}{m_e^*}$

$$\Rightarrow D_m = \frac{kT e z_m^{coll}}{m_e^* e}$$

$$\Rightarrow L_m = \sqrt{D_m \tau_m} = \sqrt{\frac{kT}{m_e^*} z_m^{coll} \tau_m^{gen}}$$

THERMO  
eq (fluct)  $\frac{1}{2} m_0^* v_{th}^2 = \frac{3}{2} kT \Rightarrow \frac{kT}{m_e^*} = \frac{v_{th}^2}{3}$

$$\Rightarrow L_m = \sqrt{\frac{v_{th}^2 z_m^{coll} \tau_m^{gen}}{3}} = \sqrt{\left( v_{th}^2 z_m^{coll} \right) \frac{\tau_m^{gen}}{3 \tau_m^{coll}}}$$

$l_{th}^2$  (mean free path between collision)

$$\Rightarrow L_m = l_m^{th} \sqrt{\frac{z_m^{gen}}{3 z_m^{coll}}}$$

$$L_p \approx l_p^{th} \sqrt{\frac{z_p^{gen}}{3 z_p^{coll}}}$$

$$z_m \sim 10^{-3}, 10^{-8}$$

$$z_m^{coll} \sim 10^{-12} - 10^{-13}$$

$$\left. \begin{aligned} z_m^{coll} &\sim 10^{-12} - 10^{-13} \\ z_m &\sim 10^{-3}, 10^{-8} \end{aligned} \right\} \frac{z_m^{gen}}{z_m^{coll}} \sim 10^{+5} \sim 10^{+9}$$

$$\sqrt{\quad} \sim 10^2 \sim 10^5$$

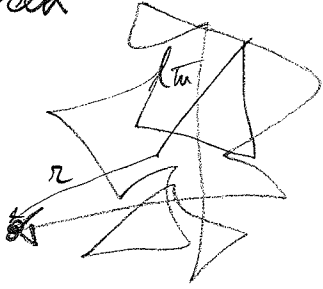
$$L_{m,ip} \sim 10^2 \sim 10^5 l_m^{th} \Rightarrow 100 - 100,000 \text{ collisions between generations}$$

why  $\sqrt{\quad}$  ?

$$\frac{2 \frac{r_{0g}}{sec}}{3 Z_p \text{ all}}$$

= N# of steps before dying  
every step jumps  $l_{th}$

Single random walk



$$r = \sum_{i=1}^N \vec{l}_i \quad |l_i| \sim l_{th}$$

$$N^E \equiv \langle r \rangle = l_{th} \sqrt{N} = l_{th} N^{1/2}$$

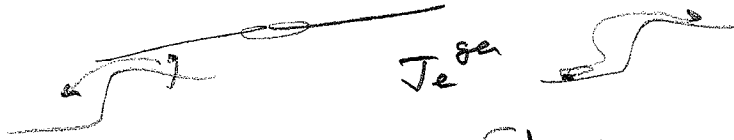
+ if free then  $\langle r \rangle \sim N^{1/2}$  (Diffusion) = NE

+ if attractive  $E < 1/2$  (SUB DIFFUSION)

+ if repulsive (volume excluded)  $E > 1/2$  (SUPER DIFFUSION)

INTERACTION BETWEEN PARTICLES

get  $J_{gen}^{hole}$

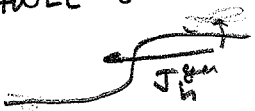


holes generated

hole number:

$$\left[ \frac{dP}{dt} \right]_{g \rightarrow r} = \frac{-(P_N(t) - P_N^0(t))}{Z_p}$$

HOLE  $g$



if  $P_N(t) \equiv 0 \Rightarrow$

holes are generated at  $\frac{P_N^0}{Z_p}$  rate (per unit volume)

are the holes (electrons)

electrons are generated

that are generated

at  $\frac{N^0 e}{Z_m}$  rate (per unit volume)

and get sucked in dipole  $\Rightarrow$

holes other side and ~~are~~ sink are electrons

must be created in a "reasonable" distance from the junction!

⇒ only if  $|x| < L_p$  (or  $L_n$ ) are useful  
 ⇒  $\epsilon$

→  $J_n^{gen} = L_p \left( \frac{p^0}{z_p} \right)$

but  $p^0$  is the eq ⇒

$p^0 n^0 = n_i^2$   
 ⇒  $p \rightarrow \tilde{N}_D$

⇒  $p^0 = \frac{n_i^2}{N_D}$

⇒  $J_n^{gen} = \left( \frac{n_i^2}{N_D} \right) \frac{L_p}{z_p}$  (per unit surface area)  
 $J_e^{gen} = \left( \frac{n_i^2}{N_a} \right) \frac{L_n}{z_n}$

Temp ?  $n_i \sim T^{3/2} e^{-E_{sep}/2kT}$

$z_n, z_p \sim \text{const}$

$J_e^{gen} \sim e^{-E_{sep}/kT}$

$L_n, L_p$

